

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

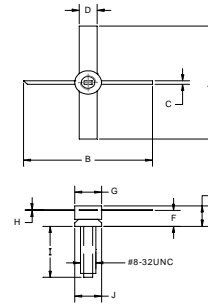
The **ASI TVU0.5B** is Designed for UHF and Television Band IV & V Applications.

FEATURES:

- Common Emitter
- $P_G = 12$ dB at 0.5 W/860 MHz
- **Omnigold™** Metalization System
- Emitter Ballasting.

MAXIMUM RATINGS

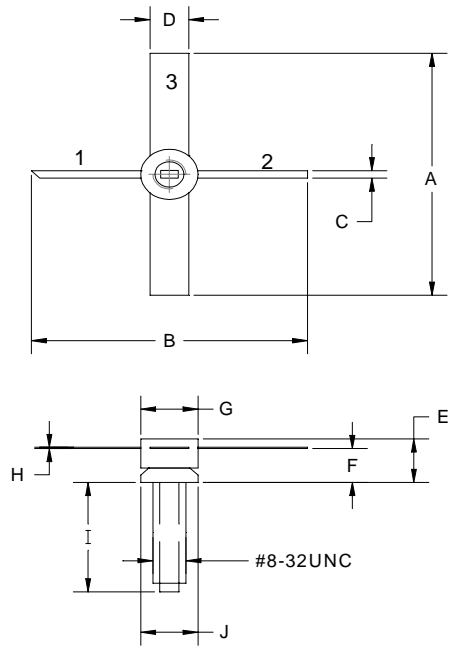
I_C	2.0 A
V_{CBO}	45 V
V_{CEO}	25 V
V_{EBO}	3.5 V
P_{DISS}	31.8 W
T_J	-65 °C to +200 °C
T_{STG}	-55 °C to +150 °C

PACKAGE STYLE .205 4L STUD


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.976 / 24.800	1.000 / 25.4000
B	.976 / 24.800	1.000 / 25.4000
C	.028 / 0.700	.031 / 0.800
D	.138 / 3.500	
E	.161 / 4.100	.196 / 5.000
F	.098 / 2.500	.110 / 2.800
G	.200 / 5.100	.208 / 5.300
H	.004 / 0.100	.006 / 0.150
I	.425 / 10.800	.465 / 11.800
J	.200 / 5.100	2.05 / 5.200

ORDER CODE: ASI10642
CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0$ mA	45			V
BV_{CE}	$I_C = 20$ mA	24			V
BV_{EBO}	$I_E = 0.25$ mA	3.5			V
I_{CBO}	$V_{CB} = 28$ V			0.45	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ mA	15		120	---
P_G IMD_1	$V_{CE} = 20$ V $I_C = 150$ mA $f = 860$ MHz $P_{OUT} = 0.5$ W $f_1 = 860$ MHz (08 dBc), $f_2 = 863.5$ MHz (-16 dBc), $f_3 = 864.5$ MHz (-7dBc)	12 -58			dB dBc



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1 = Collector 2 = Base 3 = Emitter